

INTRODUCE:

HVGT high voltage axial lead rectifier assembly is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. High current . low forward voltage
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic precipitators.
3. General purpose high voltage rectifier.
4. Microwave circuit.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: radial welding lead.
3. Net weight: 11.0 grams (approx).

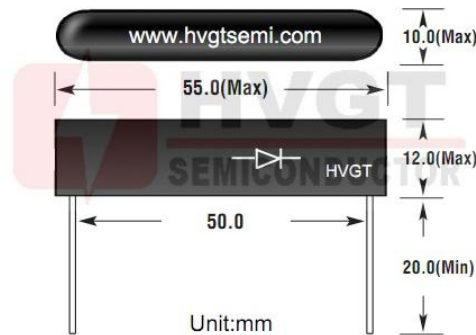
SHAPE DISPLAY:



SIZE: (Unit:mm) HVGT NAME: HVR-101255H

HVR-101255H Series

Lead Diameter 1.20mm ±0.02



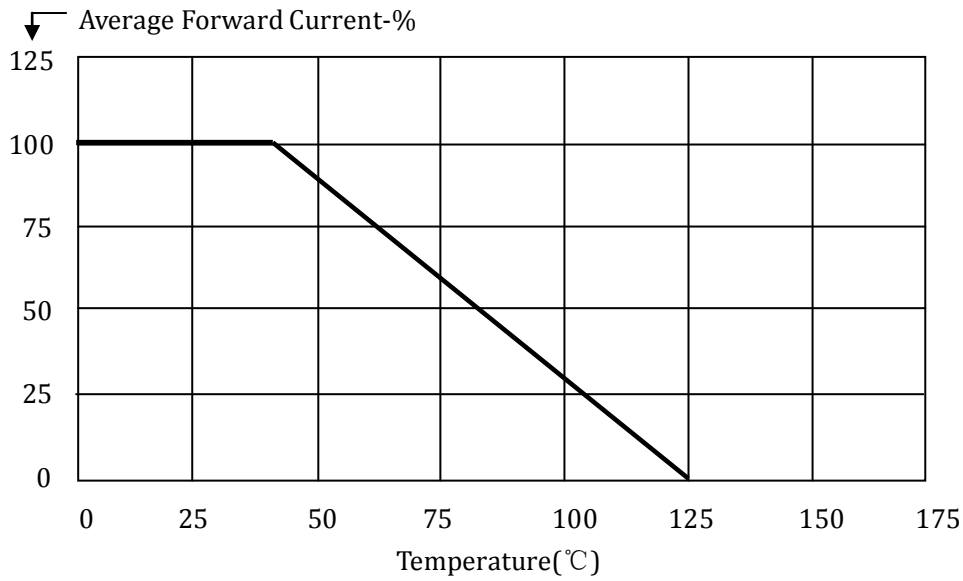
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	12.0	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	14.4	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=40^{\circ}C$	1.0	A
		$T_{OIL}=55^{\circ}C$	1.5	A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3mS	20	A
Junction Temperature	T_J		125	$^{\circ}C$
Allowable Operation Case Temperature	T_c		-40~+125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150	$^{\circ}C$

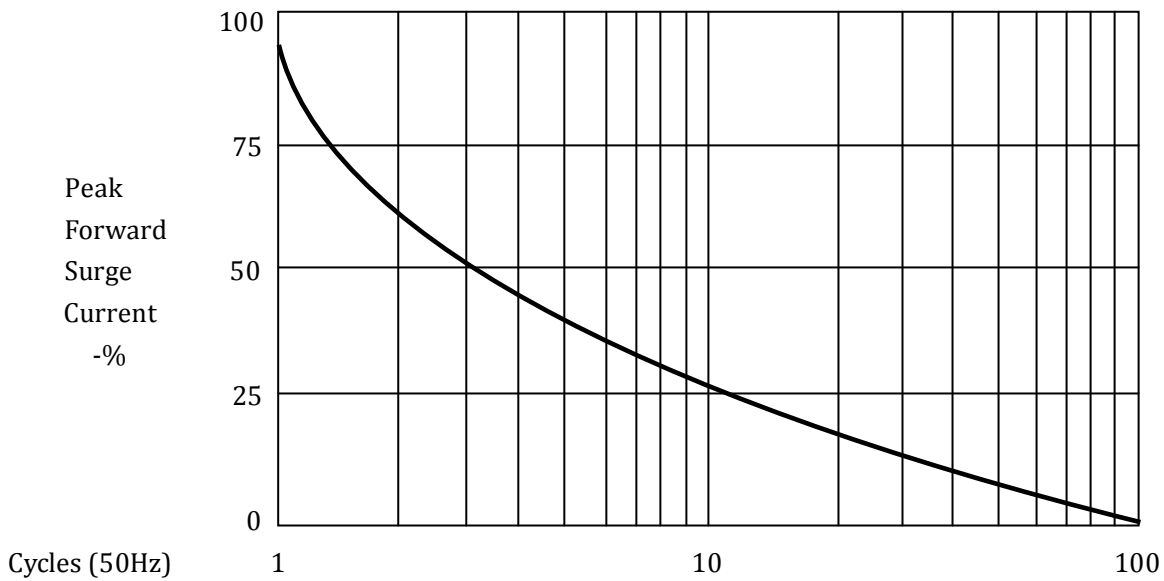
ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	14.4	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_f=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--	pF

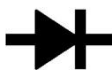
Forward Current Derating Curve



Non-Repetitive Surge Current



MARKING:

Type	Code	Cathode Mark
HVR5510S12	HVR5510S12 HVGT	

MODEL NOTE:

Type	Chip	I _{F(AV)}	T _{RR}	V _{RRM}
HVR	55	10	S	12
Radial Lead Assembly Series	Structure	1.0A	(U)75ns (F)100ns (S) Standard Recovery Time	10kV